

L-Band JTIDS Transistor

The high power pulsed transistor device part number IB0912L200 is designed for systems operating over the instantaneous bandwidth of 960-1215 MHz. While operating in class C mode under JTIDS pulsing conditions and $V_{CC}=44V$, this common base device supplies a minimum of 200 watts of peak pulse power. It utilizes a low loss internal input impedance matching structure to yield maximum device gain and to ease the implementation of external matching circuitry. The new generation bipolar transistor geometry utilizes a gold metallization system to achieve maximum reliability. Emitter ballast resistance is incorporated on the active cell for optimum thermal distribution and maximum reliability. All devices are 100% screened for large signal RF parameters.



Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Low Thermal Resistance
- Solder Sealed Hermetic

RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed
- Micro-strip structure on soft pc board with dielectric constant 10.2

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

Device	Freq (MHz)	V_{CC} (V)	P_{IN} (W)	RL (dB)	P_{OUT} (W)	G_P (dB)	I_C (A)	n_C (%)	Droop (dB)
505400-45	960	44	22	12	252	10.59	9.65	59.3	< 0.1
	1090	44	22	12	237	10.32	9.09	59.3	< 0.1
	1215	44	22	18	235	10.29	9.63	55.5	< 0.1

Pulse Format = JTIDS, (7μs ON / 6μs OFF) x 444, Long Term Duty Cycle = 22.7%

Power measurements made using Boonton 4500 Peak Power Analyzer

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	75	V	--
BD	Emitter-Base Voltage	V_{EBO}	--	2	V	--
BD	Storage Temperature Range	T_{STG}	-55	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.40	°C/W	$V_{CC}=44V$, Pulse format=JTIDS, $T_F=25\pm5^\circ C$, $P_{IN}=22W$, $N_C=45\%$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	75	--	V	$I_C = 40mA$, $V_{BE} = 0V$, $T_F = 25\pm5^\circ C$.
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	10	mA	$V_{CE} = 44V$, $V_{BE} = 0V$, $T_F = 25\pm5^\circ C$.
100%	DC Current Gain	H_{FE}	20	100	--	$V_{CE} = 5V$, $I_C = 500mA$, $T_F = 25\pm5^\circ C$.

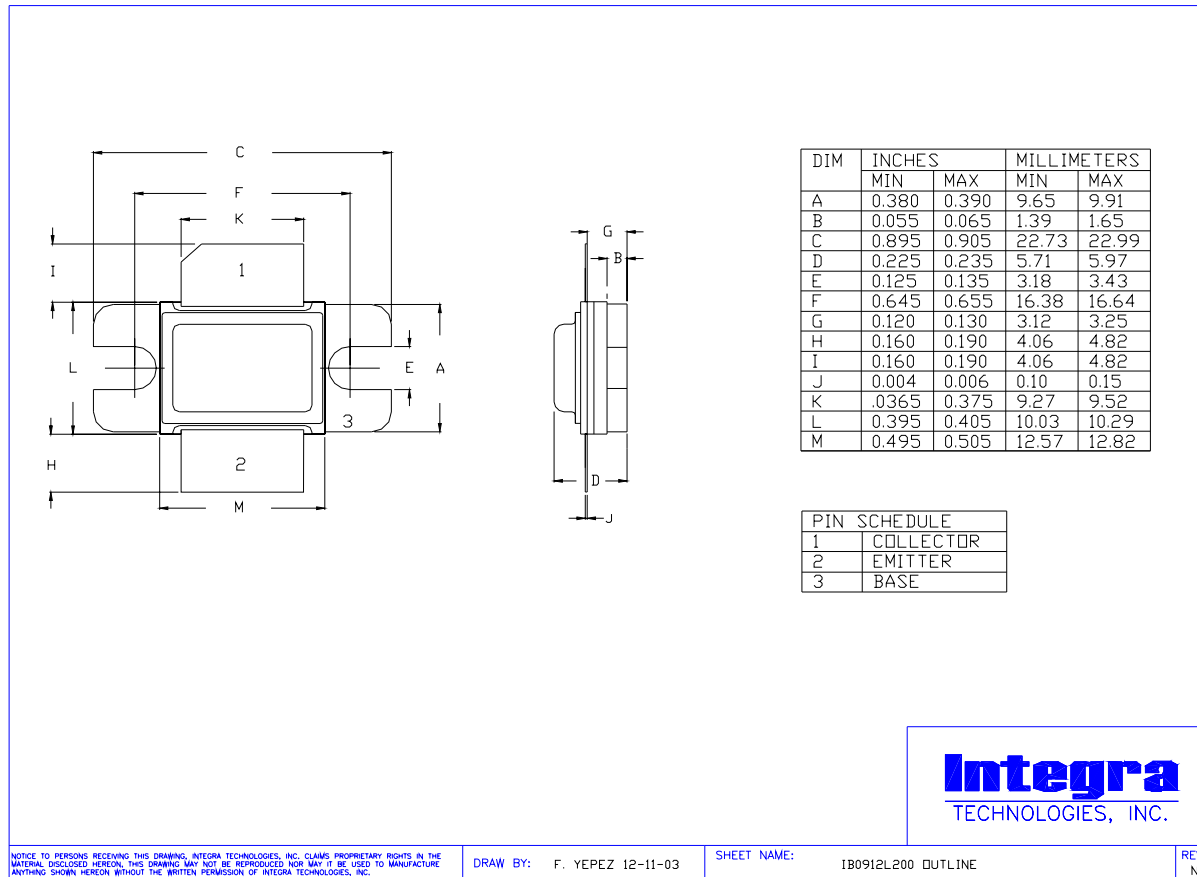
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	10	--	dB	$V_{CC}=44V$, $P_{IN}=22W$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$.
100%	Maximum Overdrive	$P_{IN(MAX)}$	--	28	W	$V_{CC}=44V$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$.
100%	Power Gain	G_P	9.6	11.1	dB	$V_{CC}=44V$, $P_{IN}=22W$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$
100%	Collector Efficiency ($P_O/I_C/V_{CC}$)	N_C	45	--	%	$V_{CC}=44V$, $P_{IN}=22W$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$.
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=44V$, $P_{IN}=22W$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$.
100%	Gain Flatness	dG		1.5	dB	Delta between highest gain and lowest gain from 960-1215MHz
100%	Stability into 1.5:1 VSWR	VSWR-S	--	--	--	$V_{CC}=44V$, $P_{IN}=22W$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$. Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	Load Mismatch Tolerance	LMT	2:1	--	--	$V_{CC}=44V$, $P_{IN}=22W$, Pulse = Note 2, $T_F=25\pm5^\circ C$, $F=F1$. Rotate 2:1 output VSWR through 360° phase. Survival.
Note 1	F1 = 960/1090/1215 MHz.					
Note 2	Pulse width = JTIDS ((7µs ON / 6µs OFF) x 444, Long Term Duty Cycle = 22.7%					
Note 3	T_F = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					

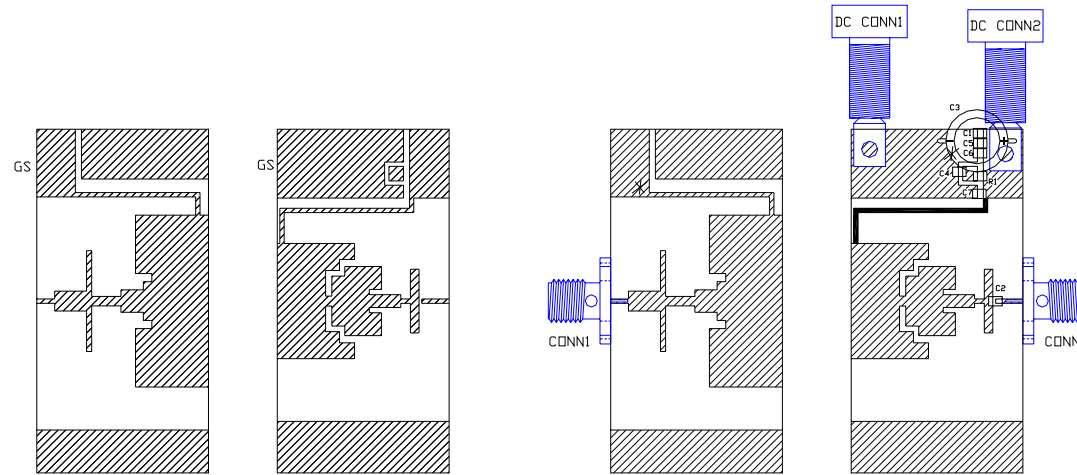
RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	Z_{IF} (Ω)	Z_{OF} (Ω)
960	1.06-j1.59	1.63-j1.73
1090	1.19-j0.97	1.85-j0.77
1215	1.42-j0.65	2.33-j0.07
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



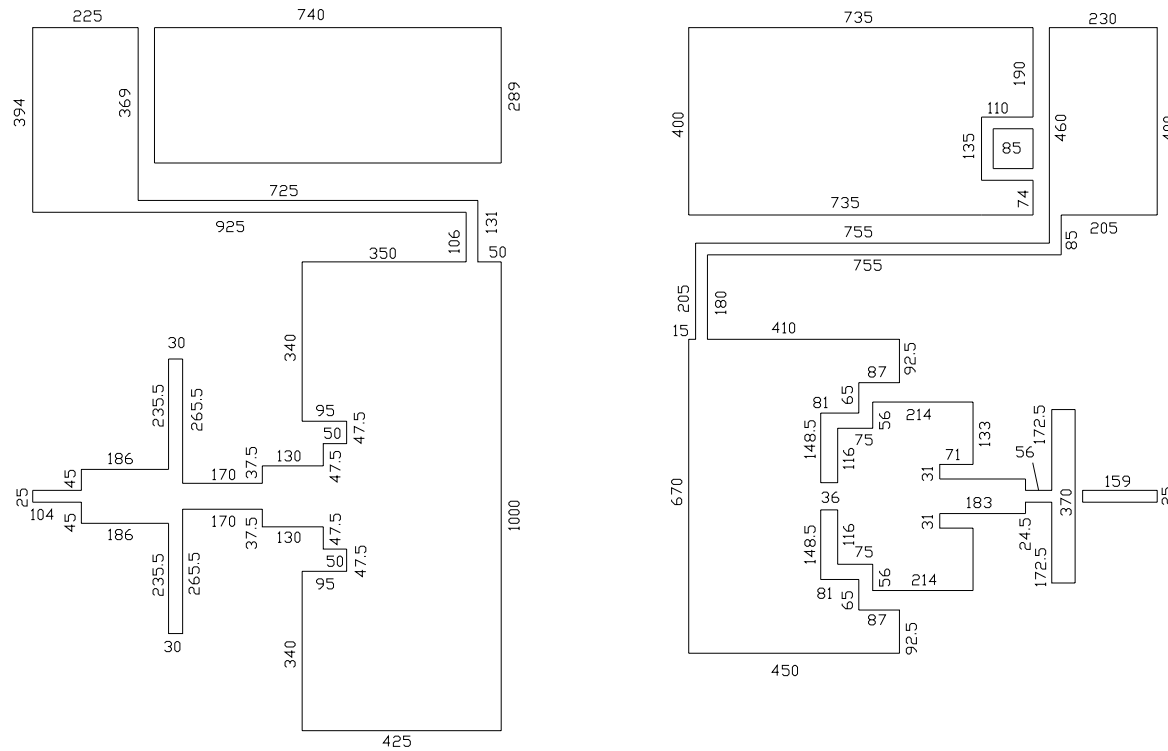
RF TEST FIXTURE



COMPONENT	DESCRIPTION
DUT	TRANSISTOR #IB0912L200, MOUNT HARD TO THE RIGHT
PC BOARD	ROGERS #RD6010.2LM .025" 1oz Cu.
C1, C2	CHIP CAPACITOR, TYPE ATC100A, 100 pF
C3	ELECTROLYTIC CAPACITOR, 68uF / 6.3V
C4	CHIP CAPACITOR 0.1uF
C5	CAPACITOR 2uF
C6	CAPACITOR 4.7nF 100V K9624 CK05 BX 472K
C7	CHIP CAPACITOR ATC 39pF
C8 (NOT SHOWN)	STORAGE ELECTROLYTIC CAPACITOR 4700uF/50V
R1	CHIP RESISTOR 6.8 OHMS
GS	GROUND SHIM, COPPER, TH=0.001"
CONN1, CONN2	SMA CONNECTOR, TYPE DS #2052-5636-02
INPUT PC BOARD CARRIER	1.00 INCH BRASS - 03
OUTPUT PC BOARD CARRIER	1.00 INCH BRASS - 03
TRANSISTOR CARRIER	2 INCH COPPER - 02
TRANSISTOR CLAMP	NORYL CLAMP -02
HEATSINK	2 INCH HEATSINK - 11
DC CONN1	BANANA JACK, BLACK
DC CONN2	BANANA JACK, RED
BLW	BIAS LINE WIRE - COPPER - 0.022" DIA TYPICAL
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

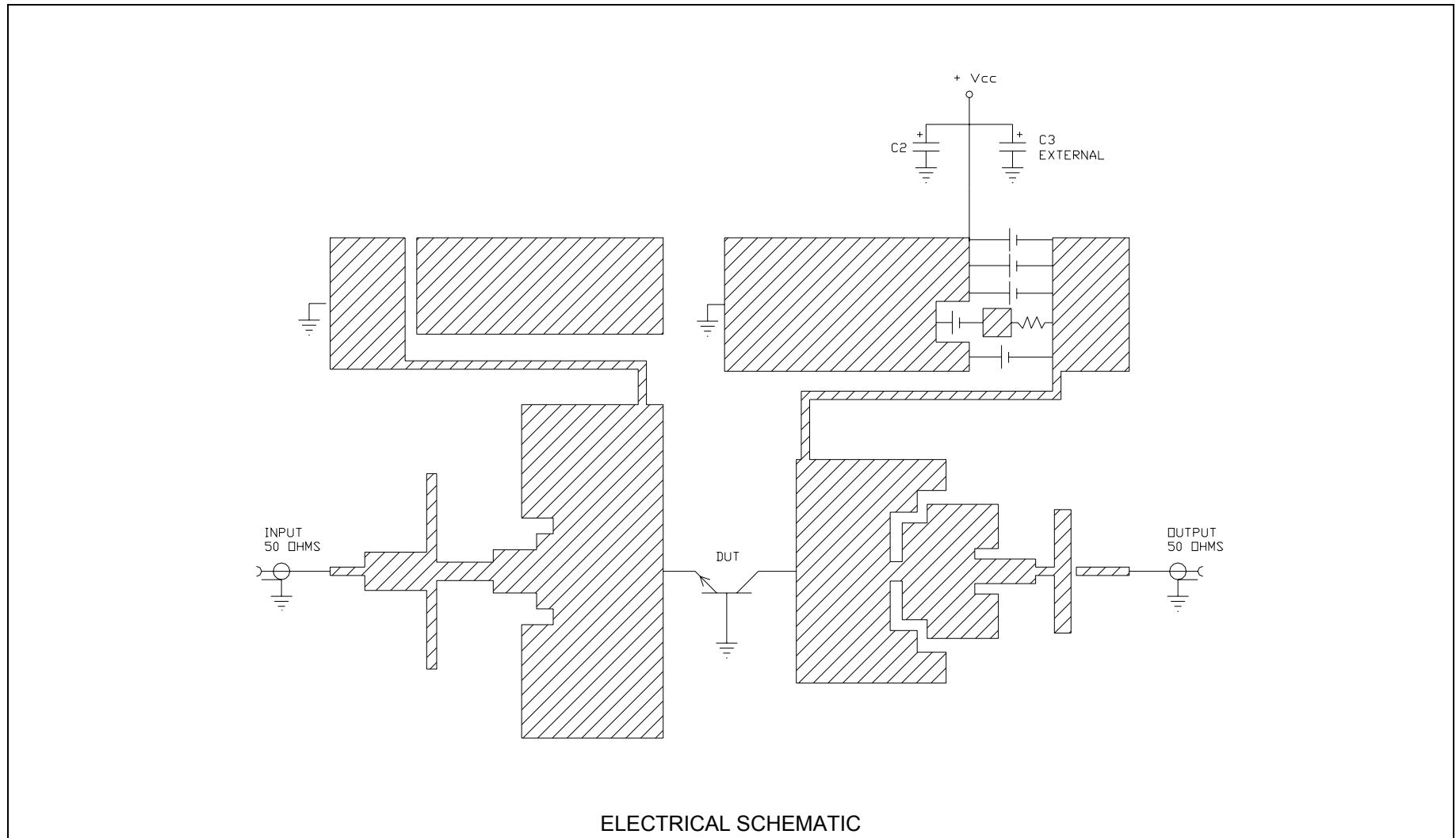
ASSEMBLY AND PARTS LIST

RF TEST FIXTURE



CIRCUIT DIMENSIONS

RF TEST FIXTURE



DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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